

OBSOLETE – PART DISCONTINUED

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
700V	0.6Ω @ V _{GS} = 10V	8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

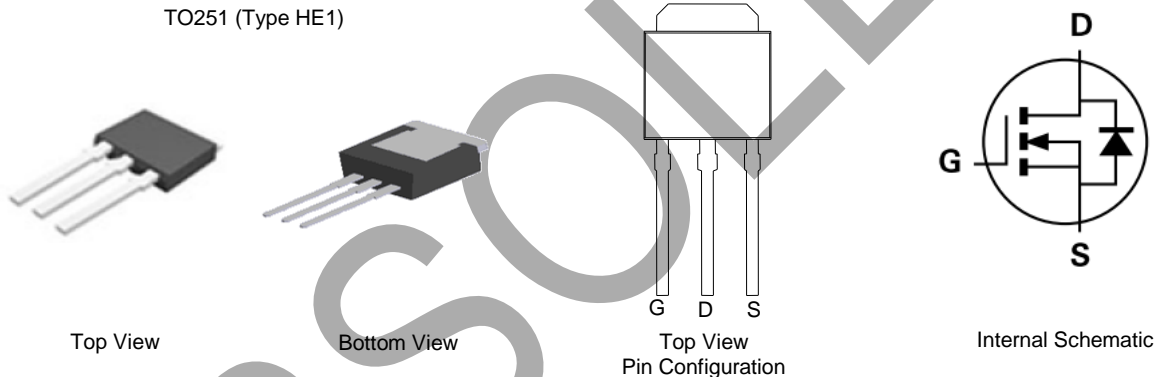
- Adaptors
- LCD & PDP TVs
- Lightings

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: TO251
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



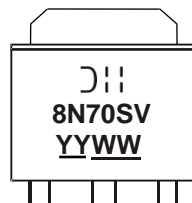
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMJ70H601SV3	TO251 (Type HE1)	75 Pieces	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

TO251 (Type HE1)



= Manufacturer's Marking
 8N70SV = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Last Two Digits of Year (ex: 22 = 2022)
 WW or WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	700	V
Gate-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = 10V	I _D	T _C = +25°C	8
		T _C = +100°C	6.4
Maximum Body Diode Forward Current (Note 6)	I _S	4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	15	A
Avalanche Current (Note 7)	I _{AS}	1.7	A
Avalanche Energy (Note 7)	E _{AS}	86	mJ
Peak Diode Recovery dv/dt (Note 7)	dv/dt	7	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _C = +25°C	125
		T _C = +100°C	50
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	72	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	1.0	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	700	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 700V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±30V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	3.4	4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.5	0.6	Ω	V _{GS} = 10V, I _D = 2.1A
Diode Forward Voltage	V _{SD}	—	0.85	1.3	V	V _{GS} = 0V, I _S = 2.1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	686	—	pF	V _{DS} = 50V, f = 1MHz, V _{GS} = 0V
Output Capacitance	C _{oss}	—	267	—		
Reverse Transfer Capacitance	C _{rss}	—	8	—		
Gate Resistance	R _G	—	2.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	20.9	—	nC	V _{DD} = 560V, I _D = 8A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	3.0	—		
Gate-Drain Charge	Q _{gd}	—	9.4	—		
Turn-On Delay Time	t _{d(ON)}	—	10	—	ns	V _{DD} = 350V, V _{GS} = 10V, R _G = 4.7Ω, I _D = 8A
Turn-On Rise Time	t _r	—	23	—		
Turn-Off Delay Time	t _{d(OFF)}	—	32	—		
Turn-Off Fall Time	t _f	—	17	—		
Body Diode Reverse Recovery Time	t _{RR}	—	261	—	ns	I _S = 8A, di/dt = 100A/µs
Body Diode Reverse Recovery Time (T _J = +150°C)	t _{RR}	—	337	—	ns	
Body Diode Reverse Recovery Charge	Q _R	—	3.0	—	µC	
Body Diode Reverse Recovery Charge (T _J = +150°C)	Q _R	—	4.0	—	µC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 - Guaranteed by design. Not subject to production testing.
 - Short duration pulse test used to minimize self-heating effect.

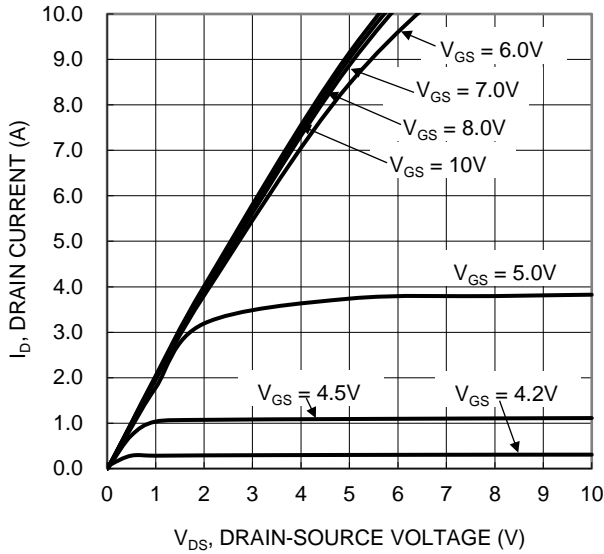


Figure 1. Typical Output Characteristic

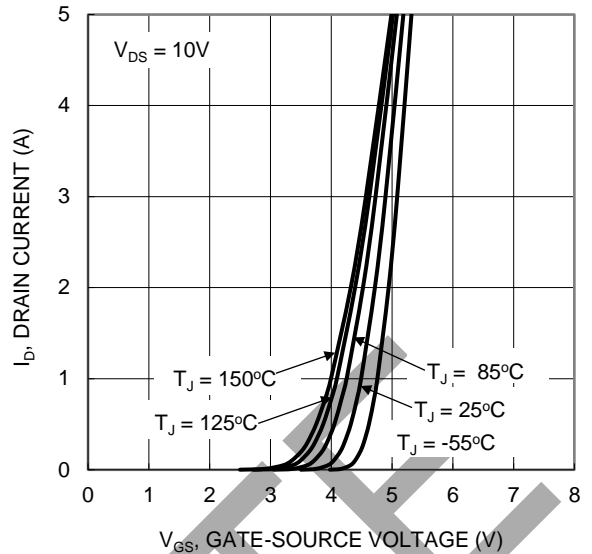


Figure 2. Typical Transfer Characteristic

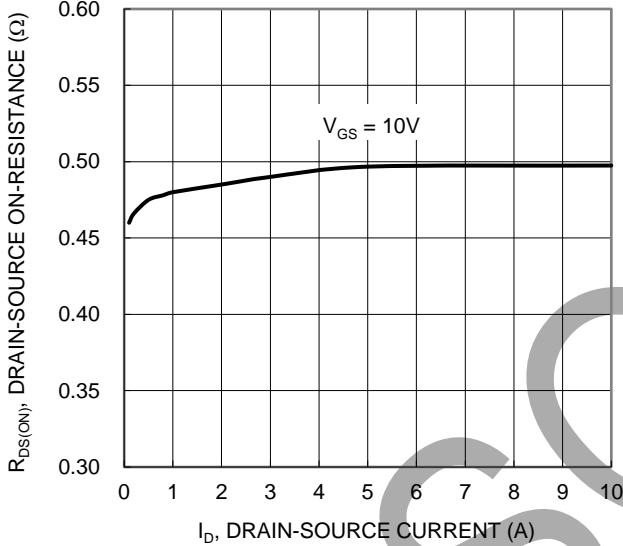


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

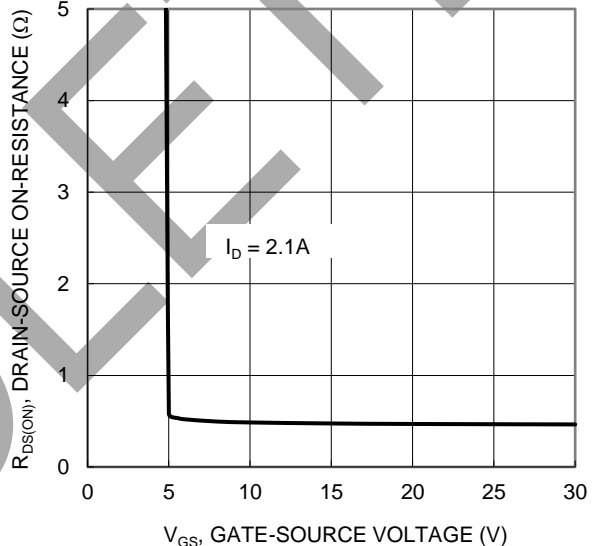


Figure 4. Typical Transfer Characteristic

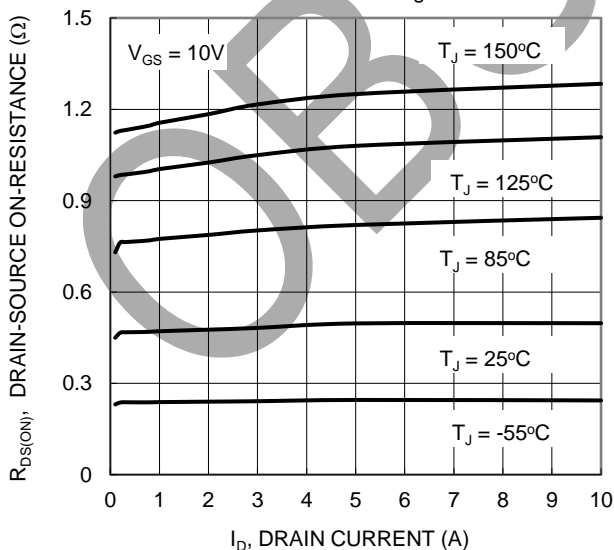


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

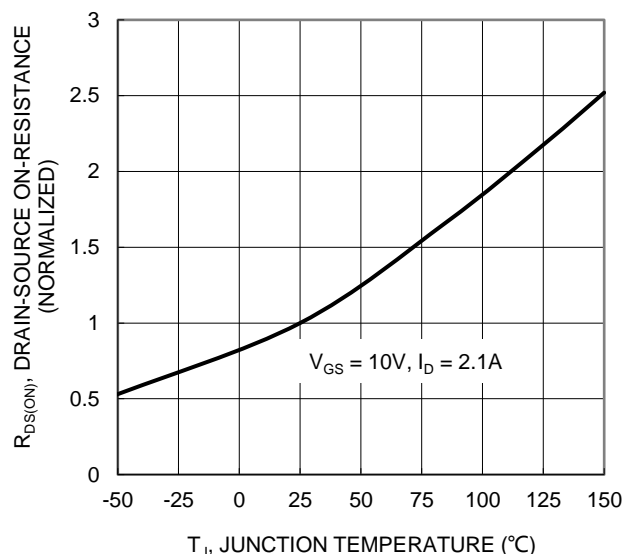
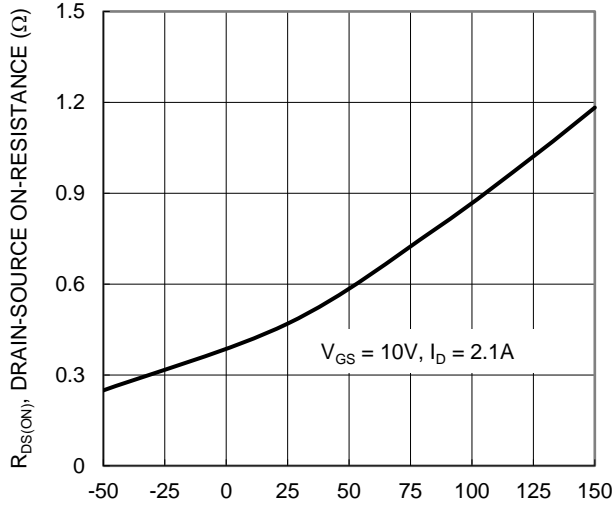
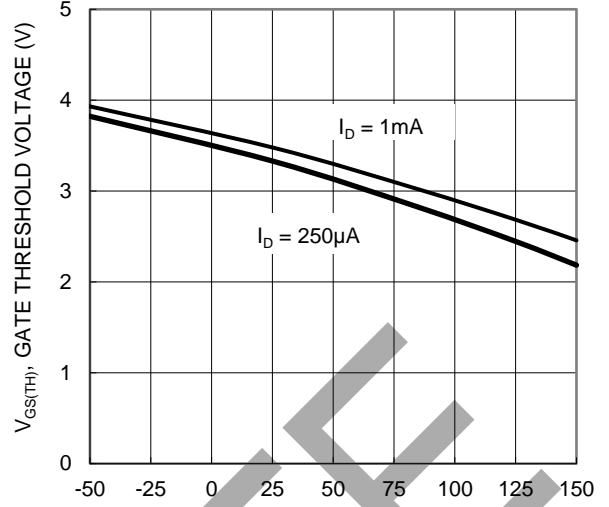


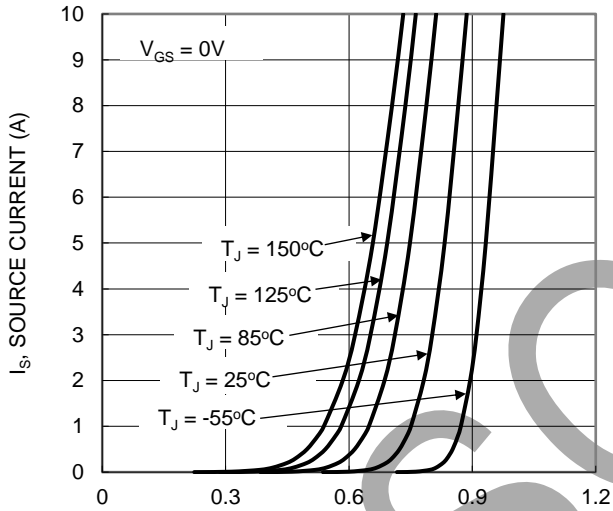
Figure 6. On-Resistance Variation with Temperature



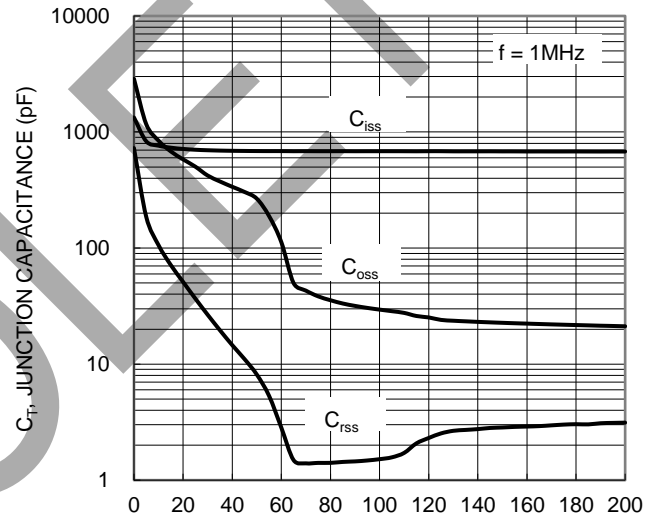
T_J , JUNCTION TEMPERATURE (°C)
Figure 7. On-Resistance Variation with Temperature



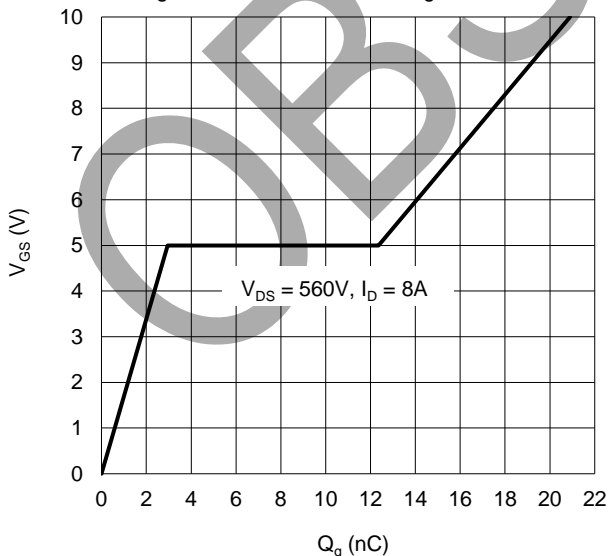
T_J , JUNCTION TEMPERATURE (°C)
Figure 8. Gate Threshold Variation vs. Junction Temperature



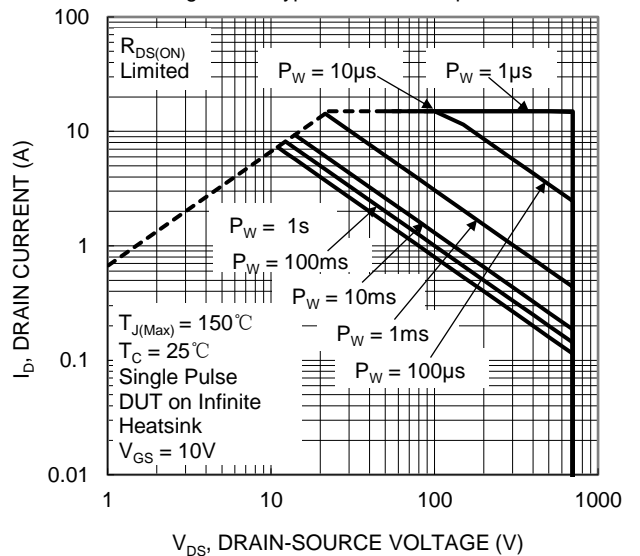
V_{DS} , SOURCE-DRAIN VOLTAGE (V)
Figure 9. Diode Forward Voltage vs. Current



V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 10. Typical Junction Capacitance



Q_g (nC)
Figure 11. Gate Charge



V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 12. SOA, Safe Operation Area

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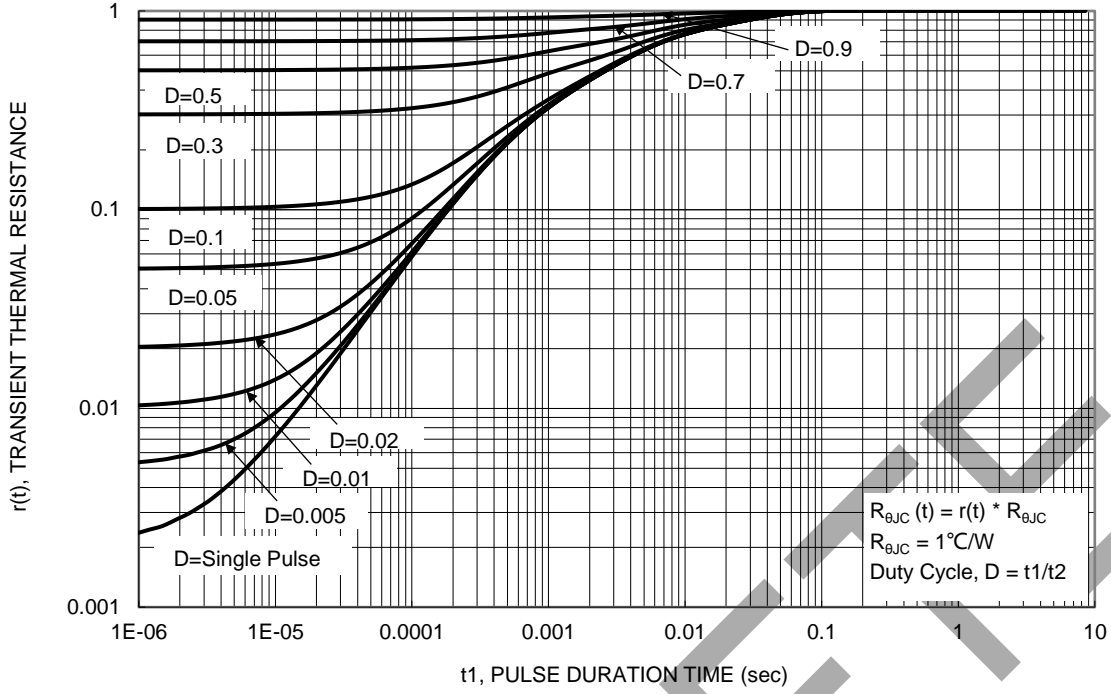


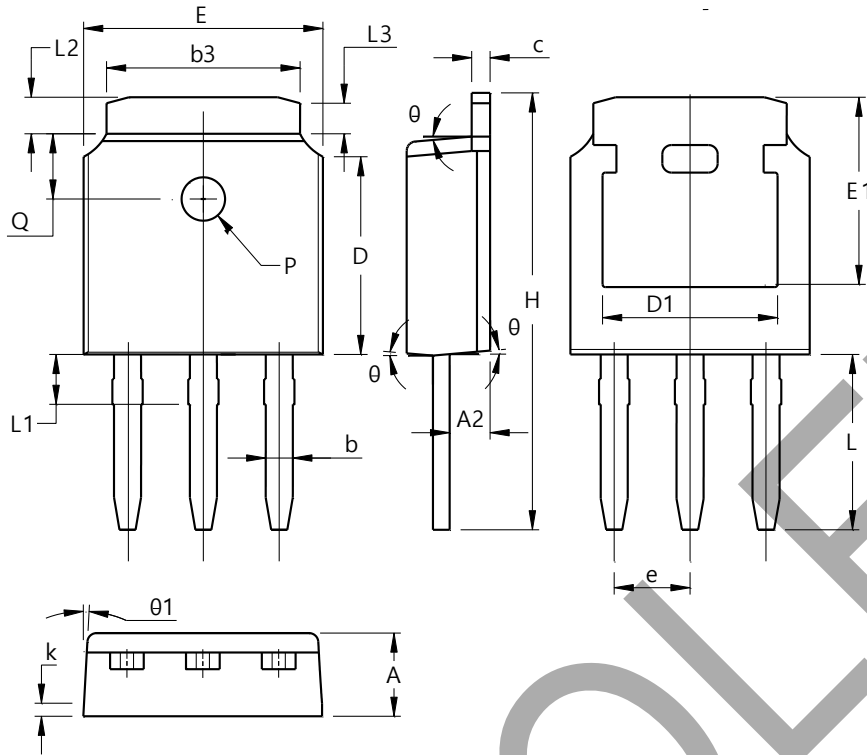
Figure 13. Transient Thermal Resistance

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Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO251 (Type HE1)



TO251 (Type HE1)			
Dim	Min	Max	Typ
A	2.20	2.40	2.30
A2	0.97	1.17	1.07
b	0.68	0.90	0.78
b3	5.20	5.50	5.33
c	0.43	0.63	0.53
D	5.98	6.22	6.10
D1	5.30 REF		
e	2.286 BSC		
E	6.40	6.80	6.60
E1	4.63	5.03	4.83
H	10.00	11.44	11.22
k	0.40REF		
L	3.90	4.30	4.10
L1	0.85	1.25	1.05
L2	0.88	1.28	1.02
L3	0.75 REF		
Q	1.65	1.95	1.80
PØ	1.20		
θ	5°	9°	7°
θ1	5°	9°	7°
All Dimensions in mm			

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